In the Claims:

Claim 1 (Original). A method for fabricating a precious-metal electrode for a storage capacitor, which comprises:

providing a substrate;

applying a catalytically inactive insulation to the substrate to form a catalytically inactive insulation region of the substrate;

applying a catalytically active connection region to the substrate, the catalytically active connection region being a precious metal material selected from the group consisting of a precious metal and an oxide of a precious metal;

producing the catalytically active connection region and the catalytically inactive insulation region by one of:

patterning the connection region, and

planarizing the connection region and the insulation region; and

depositing selectively the precious metal material on the catalytically active connection region by passing an

organometallic compound of a precious metal to the substrate at a temperature from 0° to 120°C.

Claims 2-3 (Canceled).

Claim 4 (Original). The method according to claim 1, wherein the temperature is from 20° to 80°C during the step of depositing selectively the precious metal material on the catalytically active connection region by passing the organometallic compound of the precious metal material to the substrate.

Claim 5 (Original). The method according to claim 4, wherein the temperature is from 40° to 70°C during the step of depositing selectively the precious metal material on the catalytically active connection region by passing the organometallic compound of the precious metal material to the substrate.

Claim 6 (Original). The method according to claim 1, which further comprises choosing the organometallic compound of a precious metal from the group consisting of $Pt(CO)_2Cl_2$, $Cp^*PtMe_2$, and $CpPtMe_3$.

Claim 7 (Original). The method according to claim 1, which further comprises using a reducing agent while depositing

selectively the precious metal material on the catalytically active connection region.

Claim 8 (Original). The method according to claim 7, which further comprises using hydrogen ($H_2$) as the reducing agent.

Claim 9 (Original). The method according to claim 1, which further comprises pressurizing from $10^{-4}$ to 10 bar during the depositing selectively of the precious metal material on the catalytically active connection region.

Claim 10 (Original). The method according to claim 9, which further comprises pressuring from $10^{-3}$ to $10^{-1}$ bar during the depositing selectively of the precious metal material on the catalytically active connection region.

Claim 11 (Original). The method according to claim 1, which further comprises selecting the catalytically inactive insulation region from the group consisting of $SiO_2$, $Si_3N_4$, $Al_2O_3$, AlN, BN, MgO, $La_2O_3$, LaN, $Y_2O_3$, YN, $Sc_2O_3$, ScN, $TiO_2$, $Ta_2O_3$, and oxides of lanthanides.

Claim 12 (Original). The method according to claim 1, which further comprises including in the catalytically active connection region elements selected from the group consisting of rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 13 (Original). The method according to claim 1, which further comprises including in the catalytically active connection region oxides of elements selected from the group consisting of rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 14 (Original). The method according to claim 1, which further comprises selecting the precious metal for the precious-metal electrode from the group consisting of platinum, palladium, rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 15 (Original). The method according to claim 1, which further comprises depositing the connection region as a layer.

Claim 16 (Currently Amended). The method according to claim ~~2~~ 1, which further comprises patterning the connection region using a hard mask.

Claim 17 (Currently amended). The method according to claim 1, which further comprises depositing the catalytically inactive insulation region as a layer.

Claim 18 (Currently Amended). The method according to claim ~~3~~ 1, wherein the planarizing step includes a CMP step.

Claim 19 (Currently Amended). A method for fabricating a precious-metal electrode for a storage capacitor, which comprises:

providing a substrate;

applying a catalytically active connection region to the substrate, the catalytically active connection region being a precious metal material selected from the group consisting of a precious metal and an oxide of a precious metal;

~~applying~~ forming a catalytically inactive insulation region ~~to~~ on the substrate;

producing ~~a~~ the catalytically active connection region and ~~a~~ the catalytically inactive insulation region by one of:

patterning the connection region, and

planarizing the connection region and the insulation region; and

depositing selectively the precious metal material on the catalytically active connection region by passing $Pt(PF_3)_4$ to the substrate at a temperature of from 80° to 150°C.

Claims 20-21 (Canceled).

Claim 22 (Original). The method according to claim 19, wherein the step of depositing selectively the precious metal material on the catalytically active connection region is conducted at a temperature from 100° to 120°C.

Claim 23 (Original). The method according to claim 19, which further comprises using a reducing agent while depositing selectively the precious metal material on the catalytically active connection region.

Claim 24 (Original). The method according to claim 23, which further comprises using hydrogen ($H_2$) as the reducing agent.

Claim 25 (Original). The method according to claim 19, which further comprises pressurizing from $10^{-4}$ to 10 bar during the step of depositing selectively the precious metal material on the catalytically active connection region.

Claim 26 (Original). The method according to claim 25, which further comprises pressuring from $10^{-3}$ to $10^{-1}$ bar during the step of depositing selectively the precious metal material on the catalytically active connection region.

Claim 27 (Original). The method according to claim 19, which further comprises selecting the catalytically inactive insulation region from the group consisting of $SiO_2$, $Si_3N_4$,

$Al_2O_3$, AlN, BN, MgO, $La_2O_3$, LaN, $Y_2O_3$, YN, $Sc_2O_3$, ScN, $TiO_2$, $Ta_2O_3$, and oxides of lanthanides.

Claim 28 (Original). The method according to claim 19, which further comprises including in the catalytically active connection region elements selected from the group consisting of rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 29 (Original). The method according to claim 19, which further comprises including in the catalytically active connection region oxides of elements selected from the group consisting of rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 30 (Original). The method according to claim 19, which further comprises selecting the precious metal for the precious-metal electrode from the group consisting of platinum, palladium, rhodium, iridium, ruthenium, osmium, and rhenium.

Claim 31 (Original). The method according to claim 19, which further comprises depositing the connection region as a layer.

Claim 32 (Currently Amended). The method according to claim ~~20~~ 19, which further comprises patterning the connection region using a hard mask.

Claim 33 (Original). The method according to claim 19, which further comprises depositing the insulation region as a layer.

Claim 34 (Currently Amended). The method according to claim ~~21~~ 19, wherein the planarizing step includes a CMP step.